<u>TOSHIBA</u>

TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC74VHC573F,TC74VHC573FW,TC74VHC573FT,TC74VHC573FK

Octal D-Type Latch with 3-State Output

The TC74VHC573 is an advanced high speed CMOS OCTAL LATCH with 3-STATE OUTPUT fabricated with silicon gate C2MOS technology.

It achieves the high speed operation similar to equivalent Bipolar Schottky TTL while maintaining the CMOS low power dissipation.

This 8-bit D-type latch is controlled by a latch enable input (LE) and a output enable input (\overline{OE}).

When the \overline{OE} input is high, the eight outputs are in a high impedance state.

An input protection circuit ensures that 0 to 5.5 V can be applied to the input pins without regard to the supply voltage. This device can be used to interface 5 V to 3 V systems and two supply systems such as battery back up. This circuit prevents device destruction due to mismatched supply and input voltages.

Features

- High speed: $t_{pd} = 4.5$ ns (typ.) at V_{CC} = 5 V
- Low power dissipation: $I_{CC} = 4 \mu A \pmod{at Ta} = 25^{\circ}C$
- High noise immunity: V_{NIH} = V_{NIL} = 28% V_{CC} (min)
- Power down protection is provided on all inputs.
- Balanced propagation delays: $t_{pLH} \simeq t_{pHL}$
- Wide operating voltage range: VCC (opr) = 2 to 5.5 V

Weight

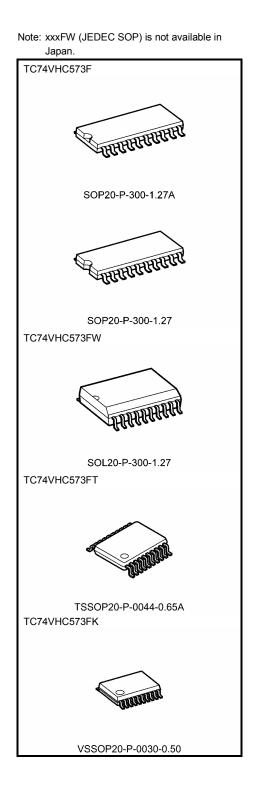
SOP20-P-300-1.27A

SOP20-P-300-1.27

SOL20-P-300-1.27

TSSOP20-P-0044-0.65A : 0.08 g (typ.) VSSOP20-P-0030-0.50 : 0.03 g (typ.)

- Low noise: VOLP = 1.2 V (max)
- Pin and function compatible with 74ALS573



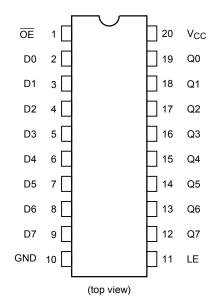
: 0.22 g (typ.)

: 0.22 g (typ.)

: 0.46 g (typ.)

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Pin Assignment



IEC Logic Symbol

0E <u>(1)</u> LE <u>(11)</u>	EN C1		
D0 (2) D1 (3) D2 (4) D3 (5) D4 (6) D5 (7) D6 (8) D7 (9)	1D		(19) Q0 (18) Q1 (17) Q2 (16) Q3 (15) Q4 (14) Q5 (13) Q6 (12) Q7

Truth Table

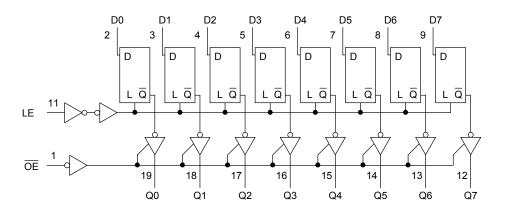
	Inputs	Output			
ŌE	LE	D	Output		
Н	Х	Х	Z		
L	L	Х	Qn		
L	Н	L	L		
L	Н	Н	Н		

X: Don't care

Z: High impedance

 $\mathsf{Q}_n\!\!:\mathsf{Q}$ outputs are latched at the time when the LE input is taken to a low logic level.

System Diagram



Absolute Maximum Ratings (Note)

Characteristics	Symbol	Rating	Unit
Supply voltage range	V _{CC}	-0.5 to 7.0	V
DC input voltage	V _{IN}	-0.5 to 7.0	V
DC output voltage	V _{OUT}	-0.5 to V _{CC} + 0.5	V
Input diode current	IIK	-20	mA
Output diode current	I _{OK}	±20	mA
DC output current	IOUT	±25	mA
DC V _{CC} /ground current	ICC	±75	mA
Power dissipation	PD	180	mW
Storage temperature	T _{stg}	-65 to 150	°C

Note: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Recommended Operating Conditions (Note)

Characteristics	Symbol	Rating	Unit
Supply voltage	V _{CC}	2.0 to 5.5	V
Input voltage	V _{IN}	0 to 5.5	V
Output voltage	V _{OUT}	0 to V _{CC}	V
Operating temperature	T _{opr}	-40 to 85	°C
Input rise and fall time	dt/dv	0 to 100 (V _{CC} = 3.3 ± 0.3 V)	ns/V
	ui/uv	0 to 20 (V _{CC} = 5 \pm 0.5 V)	115/ V

Note: The recommended operating conditions are required to ensure the normal operation of the device. Unused inputs must be tied to either VCC or GND.

Electrical Characteristics

DC Characteristics

Characteristics	Symbol	Test Condition			1	「a = 25°(0	Ta −40 to	Unit		
	,			$V_{CC}\left(V\right)$	Min	Тур.	Max	Min	Max		
High-level input V _{IH}	N/			2.0	1.50	_	-	1.50	_	v	
		—	3.0 to 5.5	V _{CC} × 0.7	—	—	V _{CC} × 0.7	—	v		
Low-level input				2.0	_	_	0.50	_	0.50		
voltage	V _{IL}		—	3.0 to 5.5	_	_	V _{CC} × 0.3	_	V _{CC} × 0.3	V	
				2.0	1.9	2.0	_	1.9	_		
		V _{IN} = V _{IH} or	I _{OH} = -50 μA	3.0	2.9	3.0	—	2.9	—		
High-level output voltage	V _{OH}			4.5	4.4	4.5	-	4.4	_	V	
Ŭ		VIL	I _{OH} = −4 mA	3.0	2.58	Ι		2.48	—		
		IO	I _{OH} = −8 mA	4.5	3.94		-	3.80	—		
		V _{IN} = V _{IH} or		2.0		0.0	0.1		0.1		
			I _{OL} = 50 μA	3.0	—	0.0	0.1	—	0.1		
Low-level output voltage	V _{OL}			4.5	_	0.0	0.1	-	0.1	V	
Ū.		VIL	I _{OL} = 4 mA	3.0		Ι	0.36		0.44	1	
			I _{OL} = 8 mA	4.5	_		0.36	-	0.44		
3-state output off-state current	I _{OZ}	V _{IN} = V _{IH} or V _{IL} V _{OUT} = V _{CC} or GND		5.5	Ι	_	±0.25	-	±2.50	μA	
Input leakage current	I _{IN}	V _{IN} = 5.5 V or GND		0 to 5.5	_	_	±0.1		±1.0	μA	
Quiescent supply current	ICC	V _{IN} = V _C	_C or GND	5.5	_	_	4.0		40.0	μA	

Timing Requirements (input: $t_r = t_f = 3 \text{ ns}$)

Characteristics	Symbol	Test Condition	Test Condition		25°C	Ta = -40 to 85°C	Unit	
			V _{CC} (V)	Тур.	Limit	Limit		
Minimum pulse width	t an		3.3 ± 0.3	_	5.0	5.0	ns	
(LE)	^t w (H)	—	5.0 ± 0.5	—	5.0	5.0	115	
Minimum och un fime	_		3.3 ± 0.3	_	3.5	3.5	20	
Minimum set-up time	ts	—	5.0 ± 0.5	—	3.5	3.5	ns	
Minimum hold time t _h		3.3 ± 0.3	_	1.5	1.5	20		
	۰h	_	5.0 ± 0.5	_	1.5	1.5	ns	

AC Characteristics (input: t_r = t_f = 3 ns)

Characteristics Symbol		Tes	st Condition		Ta = 25°C			Ta −40 to	Unit				
	- ,		V _{CC} (V)	C _L (pF)	Min	Тур.	Max	Min	Max				
		3.3 ± 0.3	15	_	7.6	11.9	1.0	14.0					
Propagation delay time	t _{pLH}		5.5 ± 0.5	50	_	10.1	15.4	1.0	17.5	ns			
(LE-Q)	t _{pHL}		5.0 ± 0.5	15	I	5.0	7.7	1.0	9.0	113			
			5.0 ± 0.5	50		6.5	9.7	1.0	11.0				
			3.3 ± 0.3	15	I	7.0	11.0	1.0	13.0				
Propagation delay time	t _{pLH}		5.5 ± 0.5	50		9.5	14.5	1.0	16.5	ns			
(D-Q)	t _{pHL}			5.0 ± 0.5	_	50+05	15	I	4.5	6.8	1.0	8.0	115
					50	I	6.0	8.8	1.0	10.0			
		R _L = 1 kΩ	3.3 ± 0.3	15		7.3	11.5	1.0	13.5	ns			
3-state output enable	t _{pZL}			50	I	9.8	15.0	1.0	17.0				
time	t _{pZH}			15		5.2	7.7	1.0	9.0				
			5.0 ± 0.5	50		6.7	9.7	1.0	11.0				
3-state output disable	t _{pLZ}	R _I = 1 kΩ	3.3 ± 0.3	50	I	10.7	14.5	1.0	16.5	ns			
time	t _{pHZ}	11 - 1 112	5.0 ± 0.5	50	_	6.7	9.7	1.0	11.0	115			
Output to output skew	t _{osLH}	(Note 1)	3.3 ± 0.3	50	_	_	1.5	_	1.5	ns			
	t _{osHL}	(NOLE I)	5.0 ± 0.5	50		-	1.0	_	1.0	115			
Input capacitance	C _{IN}		_		_	4	10	_	10	pF			
Output capacitance	C _{OUT}		_			6	-	—	—	pF			
Power dissipation capacitance	C _{PD}			(Note 2)	_	29	_	_	_	pF			

Note 1: Parameter guaranteed by design.

 $t_{OSLH} = |t_{pLHm} - t_{pLHn}|, t_{OSHL} = |t_{pHLm} - t_{pHLn}|$

Note 2: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

I_{CC (opr)} = C_{PD}·V_{CC}·f_{IN} + I_{CC}/8 (per latch)

And the total C_{PD} when n pcs. of latch operate can be gained by the following equation:

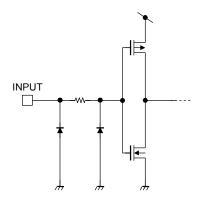
C_{PD} (total) = 21 + 8⋅n

Noise Characteristics (input: $t_r = t_f = 3 \text{ ns}$) (Note)

Characteristics	Symbol	Test Condition		Ta =	Ta = 25°C	
Characteristics	Symbol		V _{CC} (V)	Тур.	Max	Unit
Quiet output maximum dynamic	Vara	C _I = 50 pF	5.0	0.8	1.0	V
V _{OL}	V _{OLP}	CL - 50 pr	5.0	(0.9)	(1.2)	v
Quiet output minimum dynamic	Varia	C _I = 50 pF	5.0	-0.8	-1.0	V
V _{OL}	V _{OLV}	CL - 50 pr	5.0	(-0.9)	(-1.2)	v
Minimum high level dynamic input voltage	V _{IHD}	C _L = 50 pF	5.0	_	3.5	V
Maximum low level dynamic input voltage	V _{ILD}	C _L = 50 pF	5.0	_	1.5	V

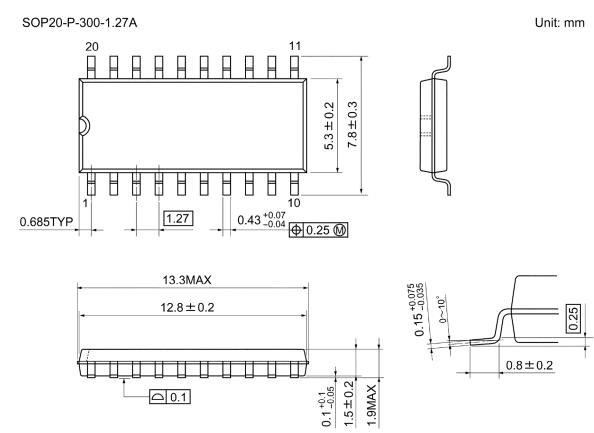
Note: The value in () only applies to JEDEC SOP (FW) devices.

Input Equivalent Circuit



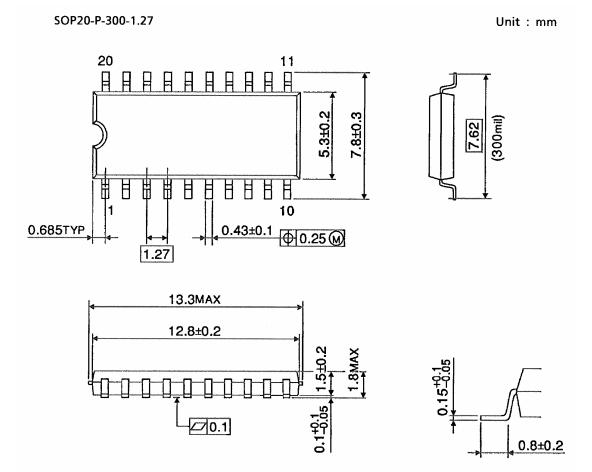
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Package Dimensions



Weight: 0.22 g (typ.)

Package Dimensions

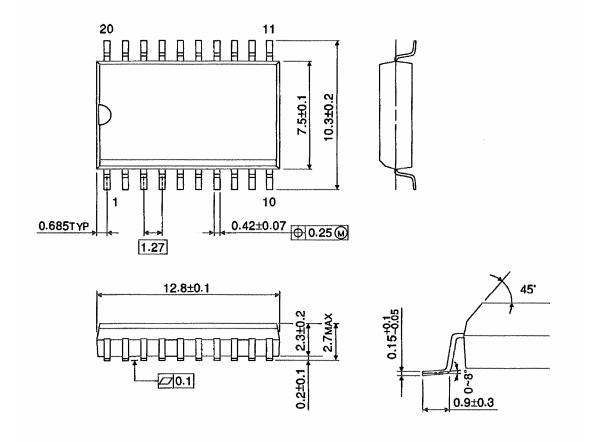


Weight: 0.22 g (typ.)

Package Dimensions (Note)

SOL20-P-300-1.27

Unit : mm



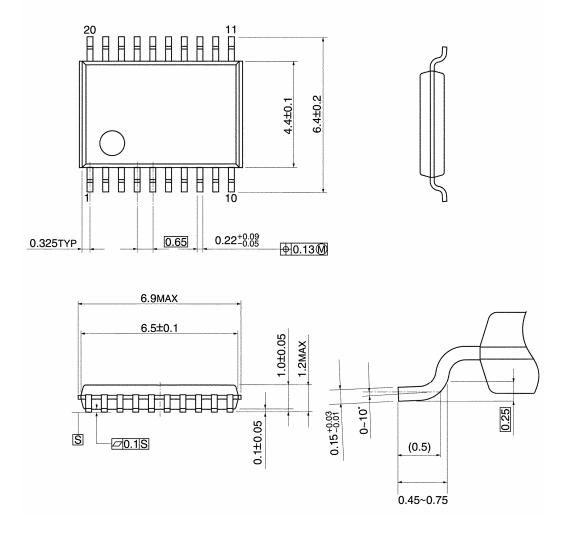
Note: This package is not available in Japan.

Weight: 0.46 g (typ.)

Package Dimensions

TSSOP20-P-0044-0.65A

Unit: mm

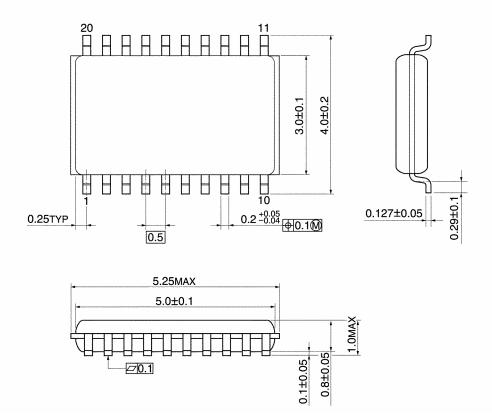


Weight: 0.08 g (typ.)

Package Dimensions

VSSOP20-P-0030-0.50

Unit: mm



Weight: 0.03 g (typ.)

Note: Lead (Pb)-Free Packages

SOP20-P-300-1.27A TSSOP20-P-0044-0.65A VSSOP20-P-0030-0.50

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Handbook" etc. 021023 A

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